



Ilaria Maticena

Tutor: Santolo Daliento

XXXIII Cycle - I year presentation

Impedance spectroscopy for
interface characterization in
semiconductor devices

Background

M.Sc.	Ph.D.
<p>Electronic Engineering Date: 14th Dec 2016</p> <p>Subject: Microelectronics <i>Prof. Vincenzo d'Alessandro</i> <i>Prof. Marco Spirito</i></p> <p>Title: <i>"Ultra-Wideband dielectric spectroscopy using an open-ended coaxial probe at MW frequencies"</i>.</p>	<p>Electronic Engineering- ING-INF/01</p> <p>Tutor: <i>Prof. Santolo Daliento</i></p> <p>Athenaeum fellowship</p> <p>Microelectronic Technologies Laboratory, Building 2, Via Claudio, 21</p> <p>Tel: +39 081 76 83800</p>

Cooperation

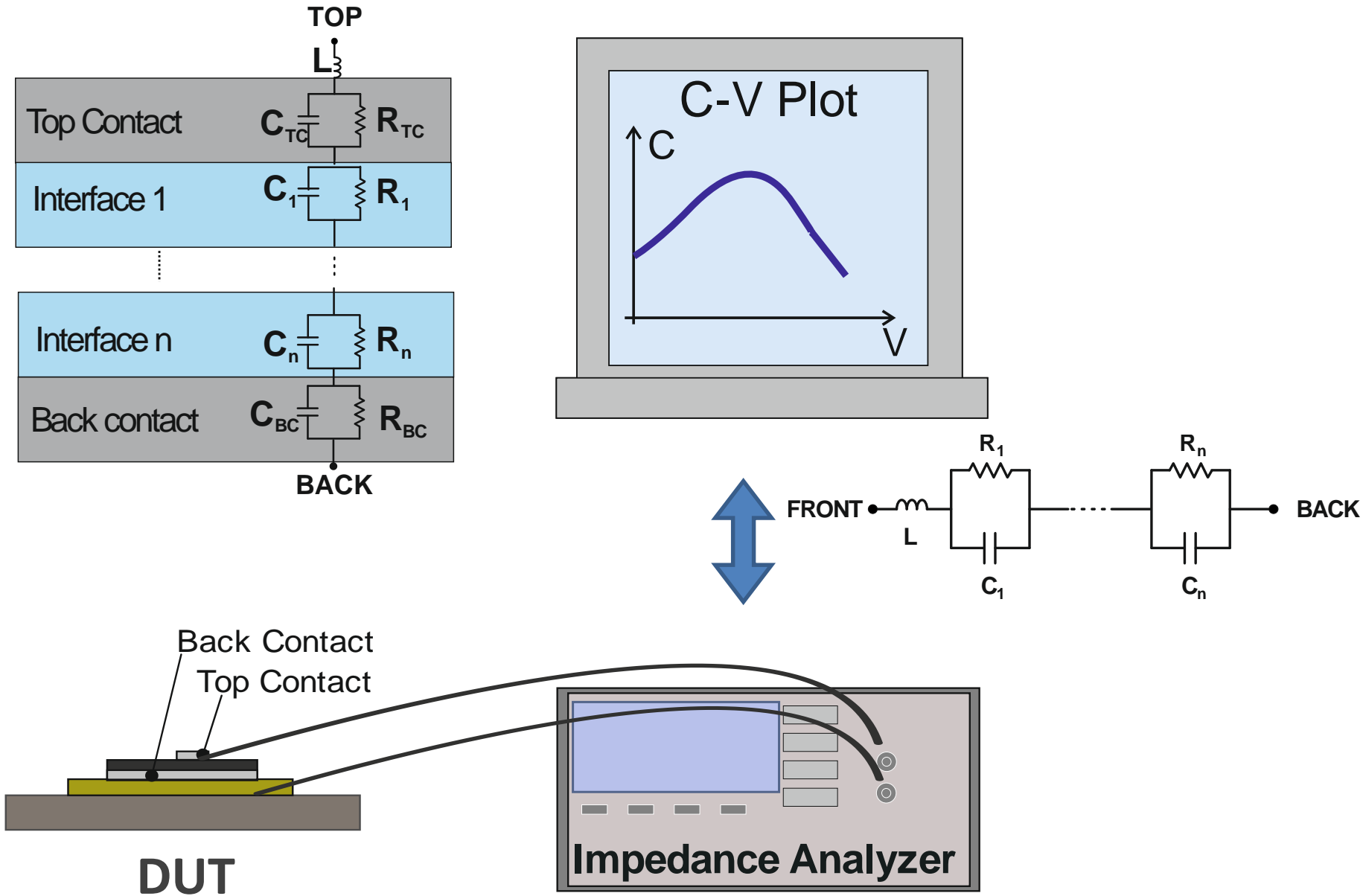
Enea Portici Research Center



Agenzia nazionale per le nuove tecnologie, l'energia e lo sviluppo economico sostenibile

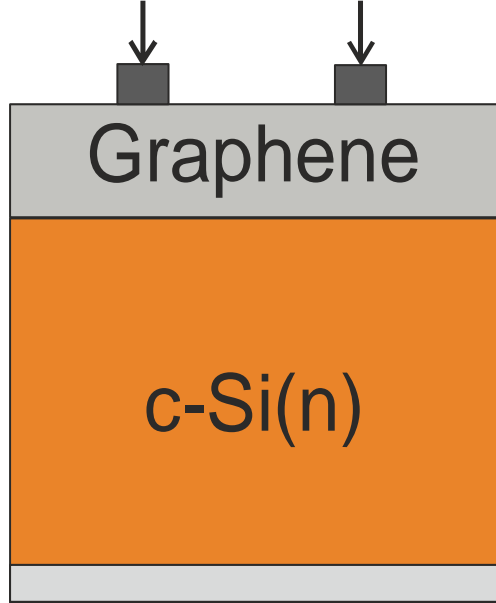


Impedance Spectroscopy

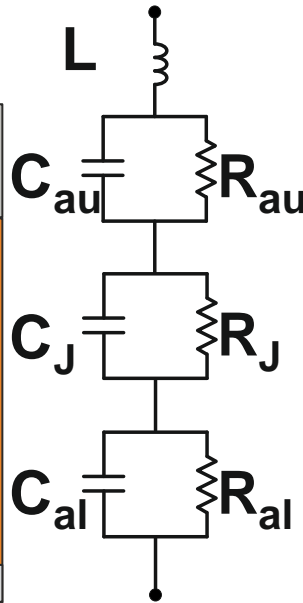


Impedance Spectroscopy for Graphene Solar Cells Characterization

Front contacts

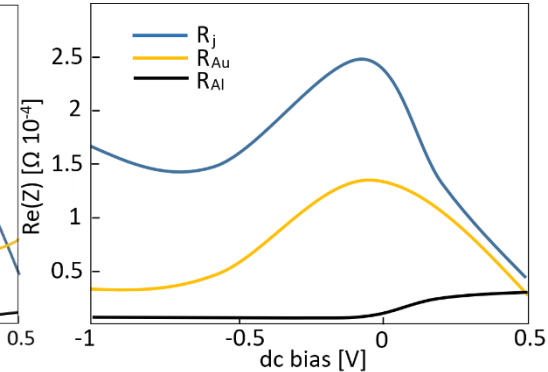
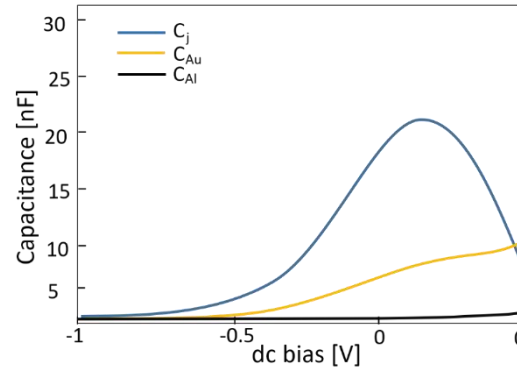
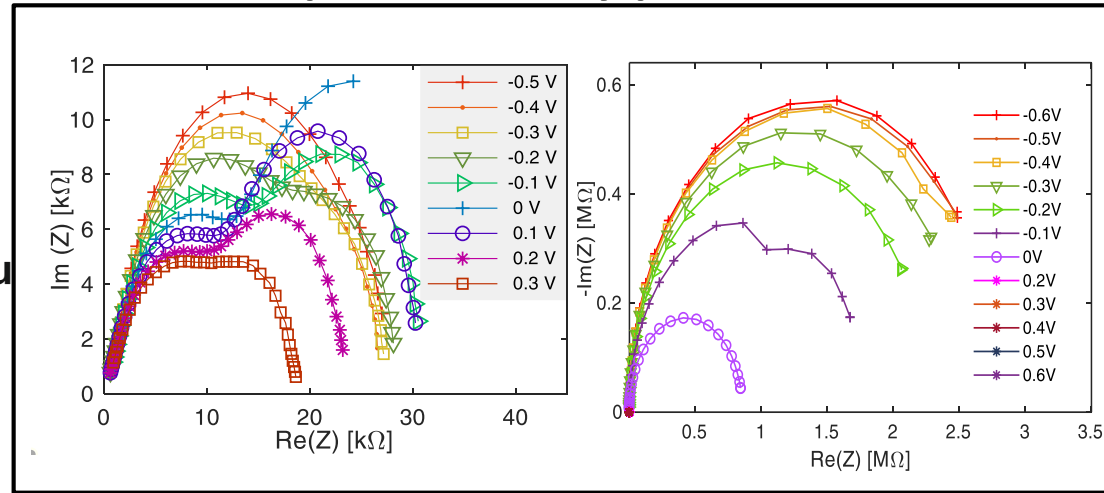


FRONT

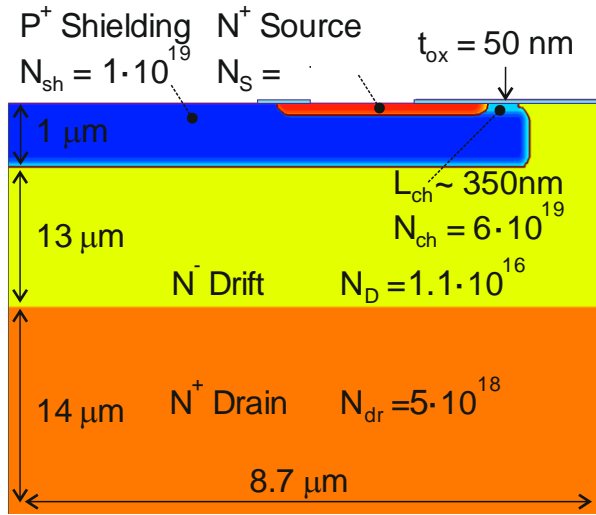


BACK

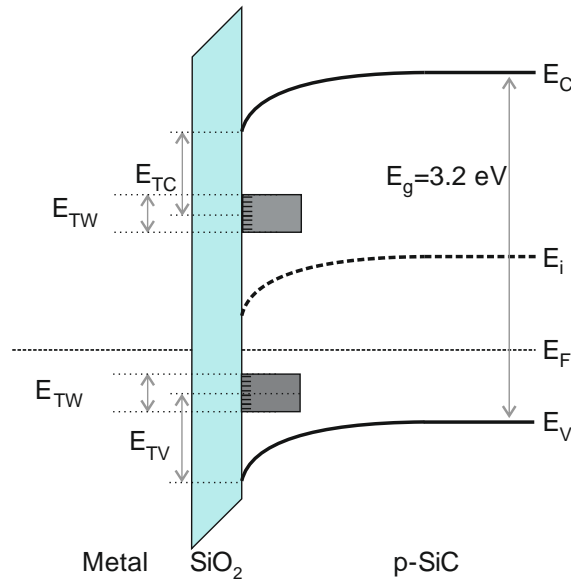
Experimental Nyquist Plots



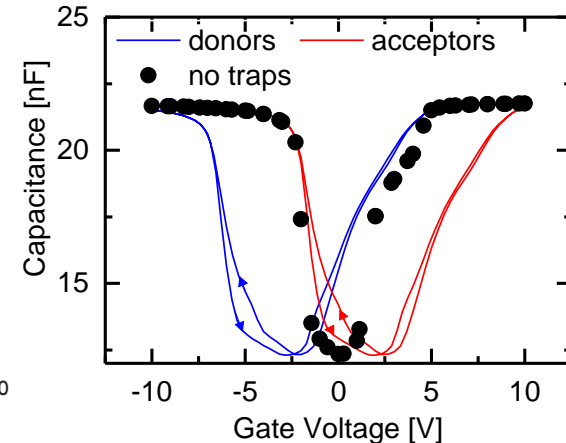
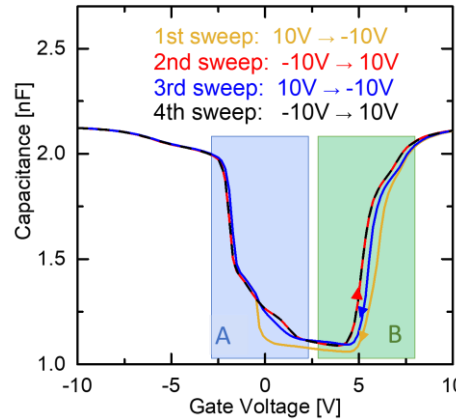
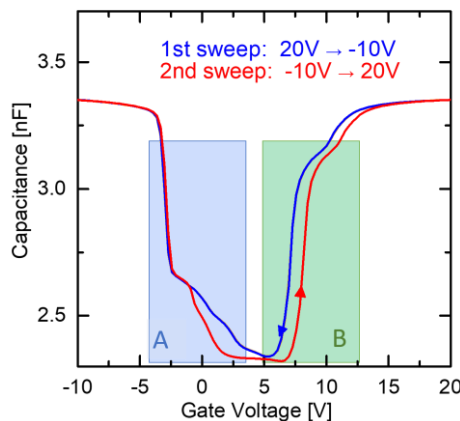
Impedance Spectroscopy for SiC Power MOSFET Characterization



SiC MOSFET TCAD structure (not in scale).



Band diagram of the structure. Traps are modeled with a square trap band distribution, where E_{TW} is the distribution width and E_{TV} and E_{TC} are the distance of the band center from the valence and conduction band, respectively



1st year production

Journal papers	Maresca, Luca, Maticena, Ilaria, Riccio, Michele, Irace, Andrea, Breglio, Giovanni and Daliento, Santolo "Evaluation of the Si/SiO ₂ interface traps distribution by C-V measurements for calibrated SiC MOSFET TCAD simulations". Journal of Emerging and Selected Topics in Power Electronics (under revision).
Conference papers	<ol style="list-style-type: none">1. P. Guerriero, I. Maticena, and S. Daliento. "Reconfiguration of solar fields by means of forced activation of bypass diodes." In 2018 International Symposium on Power Electronics, Electrical Drives, Automation and Motion (SPEEDAM), pp. 817-822. IEEE, 2018.2. I. Maticena "Avoiding the Hot Spot Occurrence". In SIE2018, 50th Annual Meeting of Associazione Societa' Italiana di Elettronica3. P. Guerriero, P. A. Cennamo, I. Maticena, and S. Daliento. "Avoiding the Hot Spot Occurrence in PV Modules." In 2018 IEEE International Conference on Environment and Electrical Engineering and 2018 IEEE Industrial and Commercial Power Systems Europe (EEEIC/I&CPS Europe), pp. 1-5. IEEE, 2018.4. I. Maticena, et al. "Impedance spectroscopy characterization of a graphene based solar cell with improved contacts", ELECTRIMACS 2019 (accepted).5. L. Lancellotti, N. Lisi, P. Delli Veneri, E. Bobeico, I. Maticena, P. Guerriero, S. Daliento "Graphene-on-Silicon solar cells with graphite contacts", ICCEP, 2019 (under revision).

Next years...

Research activity:

- Extract physical parameters from RC networks...
- Build TCAD setup to further understand interface traps distribution.
- Move this analysis to multilayer structures.

	Credits year 1								Credits year 2								Credits year 3								Total	Check
	Estimated	1	2	3	4	5	6	Summary	Estimated	1	2	3	4	5	6	Summary	Estimated	1	2	3	4	5	6	Summary		
Modules	20	0	0	4	0	9	9.4	22	10							0								0	22	30-70
Seminars	5	4	1		0.2	0	0	5.2	5	0	0	0	0		0	0								0	5.2	10-30
Research	35	6	9	6	9.8	1	0.6	32	45	0	0	0	0	0	0	0	60							0	32	80-140
	60	10	10	10	10	10	10	60	60	0	0	0	0	0	0	0	60	0	0	0	0	0	0	0	60	180